

NCE N-Channel Super Trench II Power MOSFET

Description

The NCEP018N60AGU uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

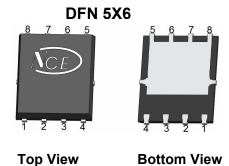
Application

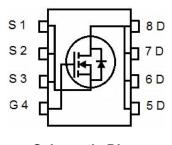
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =60V,I_D =195A
 - $$\begin{split} R_{DS(ON)} = & 1.4 \text{ m}\Omega \text{ (typical)} \textcircled{2} \text{ V}_{GS} = & 10 \text{V} \\ R_{DS(ON)} = & 1.8 \text{ m}\Omega \text{ (typical)} \textcircled{2} \text{ V}_{GS} = & 4.5 \text{V} \end{split}$$
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!





Schematic Diagram

Package Marking and Ordering Information

[Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
	P018N60AGU	NCEP018N60AGU	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	60	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	195	А
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	135	А
Pulsed Drain Current	I _{DM}	780	А
Maximum Power Dissipation	P _D	220	W
Derating factor		1.76	W/℃
Single pulse avalanche energy (Note 1)	Eas	871	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R _{eJC}	0.57	°C/W
Thermal Resistance,Junction-to-Ambient(Note 4)	R _{0JA}	50	°C/W

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Electrical Characteristics (T_C=25°C unless otherwise noted)

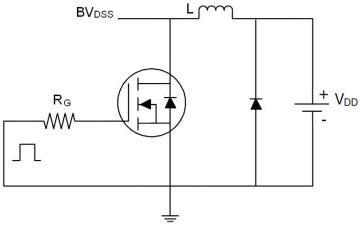
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics			<u> </u>	,		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1.0	1.7	2.5	V
Dunin Course On State Begintones	Б	V _{GS} =10V, I _D =20A	-	1.4	1.8	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A	-	1.8	2.4	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	-	50	-	S
Dynamic Characteristics	·			,		
Input Capacitance	C _{lss}		-	6150	-	PF
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, F=1.0MHz	-	965	-	PF
Reverse Transfer Capacitance	Crss	r-1.01VID2	-	65	-	PF
Switching Characteristics (Note 2)	·					
Turn-on Delay Time	t _{d(on)}		-	17	-	nS
Turn-on Rise Time	t _r	V_{DD} =30 V , I_D =20 A	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =4.7 Ω	-	60	-	nS
Turn-Off Fall Time	t _f		-	18	-	nS
Total Gate Charge	Qg	.,	-	103		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=30V,I_{D}=20A,$	-	18		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	15.5		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current	Is		-	-	195	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = I_S$	-	60		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	85		nC

Notes:

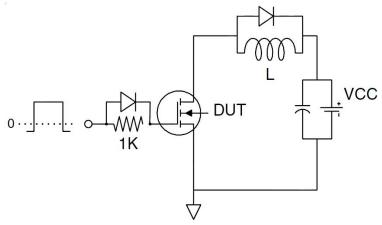
- 1. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=30V,VG=10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_J(MAX)=150°C. The SOA curve provides a single pulse rating.
- 4.The value of $R_{\theta,JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

Test Circuit

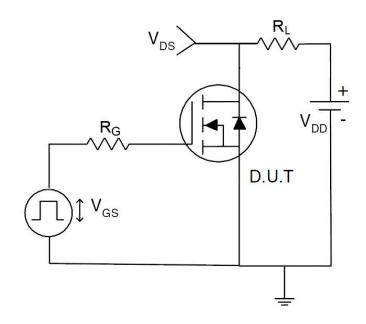
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

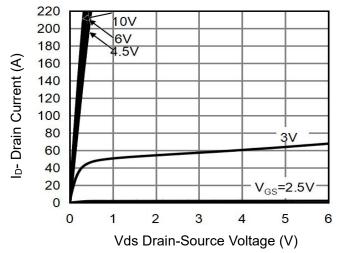


Figure 1 Output Characteristics

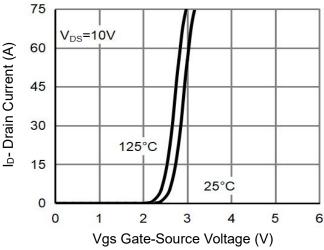


Figure 2 Transfer Characteristics

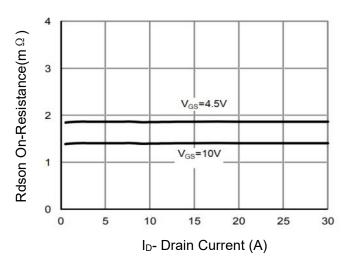


Figure 3 Rdson- Drain Current

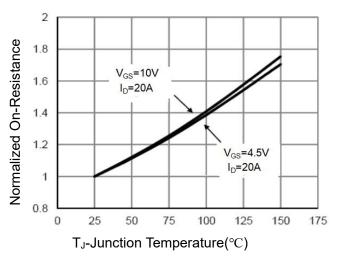


Figure 4 Rdson-JunctionTemperature

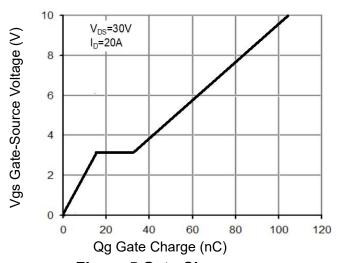


Figure 5 Gate Charge

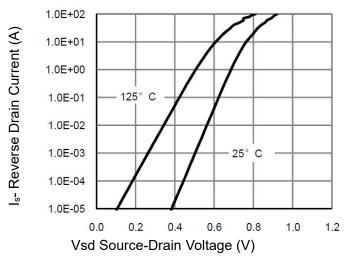


Figure 6 Source- Drain Diode Forward

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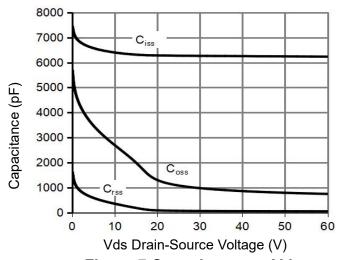


Figure 7 Capacitance vs Vds

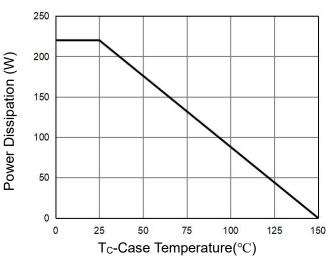


Figure 9 Power De-rating

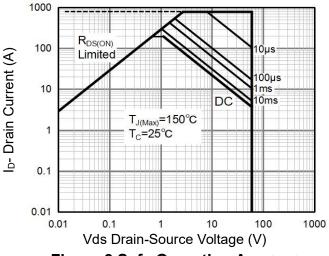


Figure 8 Safe Operation Area(Note 3)

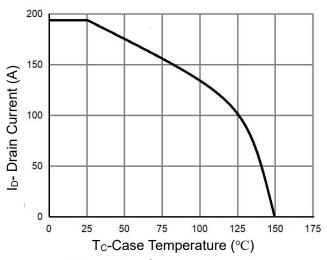


Figure 10 Current De-rating

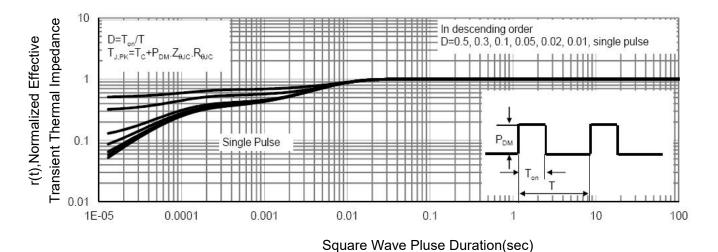
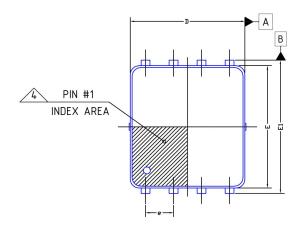
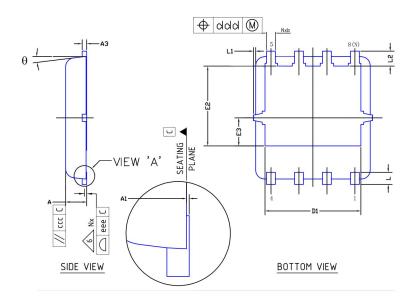


Figure 11 Normalized Maximum Transient Thermal Impedance

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DFN5X6-8L Package Information





	Dimension Table					
Thickness Symbol	٧			NOTE		
mbol os	MINIMUM NOMINA		MAXIMUM			
Α	0.85	0.95	1.00			
A1	0.00		0.05			
A3		0.2 Ref				
b	0.30	0.40	0.50			
D		5.20 BSC				
E		5.55 BSC				
е		1.27 BSC				
D1	4.25	4.35	4.45			
E1	5.95	6.05	6.15			
E2	3.525	3.625	3.725			
E3	1.175	1.275	1.375			
L	0.45	0.55	0.65			
L1	0	 0.68 REF	0.15			
L2						
θ	θ 0° 10°					
aaa		0.05				
bbb						
ccc	0.10					
ddd	0.05					
eee	0.08					
N	8			3		
ND		5				
	NOTES 1,2					
LF PART NO.	F PART NO. 445831/445897					

NOTE:

- 1. Dimensioning and tolerancing conform to ASME Y14.5-2009.
- 2. All dimensions are in millimeters.
- 3. N is the total number of terminals.
- 4. The location of the marked terminal #1 identifier is within the hatched area.
- 5. NE refers to the maximum number of terminals E side.
- 6. Coplanarity applies to the terminals and all other bottom surface metallization.

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